

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

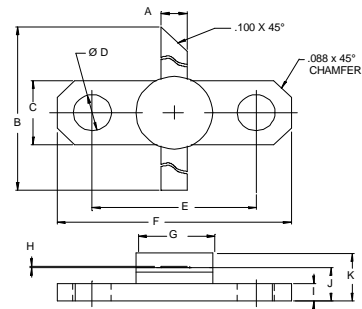
The ASI AVD002F is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CC}	37 V
P_{DISS}	10 W @ T _C ≤ 100 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	10 °C/W

PACKAGE STYLE .250 2L FLG(B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

ORDER CODE: ASI10552
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1 mA	45			V
BV_{CER}	I _C = 5 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CES}	V _{CE} = 35 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	30		300	---
P_G	V _{CC} = 35 V P _{OUT} = 2 W f = 1025 - 1150 MHz	9.0			dB
η_C		35			%